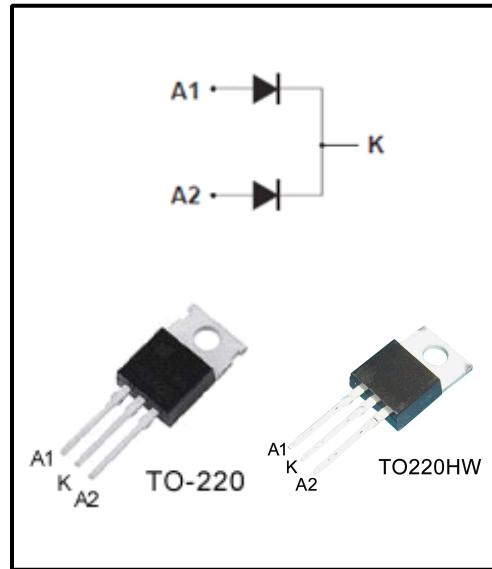


Power Schottky Rectifier

Features

- 20A(2×10A),100V
- $V_F(\text{max})=0.7\text{V}(@TJ=125^\circ\text{C})$
- Low power loss, high efficiency
- Common cathode structure
- Guard ring for over voltage protection, High reliability
- Maximum Junction Temperature Range(175°C)



General Description

Dual center tap Schottky rectifiers suited for High frequency switch power supply and Free wheeling diodes, polarity protection applications.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DRM}	Repetitive peak reverse voltage	100	V
V_{DC}	Maximum DC blocking voltage	100	V
$I_{F(AV)}$	Average forward current	per diode	10
		per device	20
I_{FSM}	Surge non repetitive forward current	200	A
T_J	Junction Temperature	175	°C
T_{stg}	Storage Temperature	-40~150	°C

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R_{QJC}	Thermal Resistance, Junction-to-Case	-	-	1.9	°C/W

Ordering Information

Order codes	Package	Marking	Halogen Free	Packaging
WSP20D100L	TO220C	P20D100L	NO	Tube
WSP20D100-HW	TO220HW	P20D100	NO	Tube

Electrical Characteristics (per diode)

Characteristics	Symbol	Test Condition		Min	Typ.	Max	Unit
Reverse leakage current	I_R	VR = VRRM	T _j = 25°C	-	-	10	µA
			T _j = 125°C		-	5	mA
Forward voltage drop	V_F	IF= 10A	T _j = 25°C	-	0.78	0.85	V
			T _j = 125°C	-	0.65	0.7	

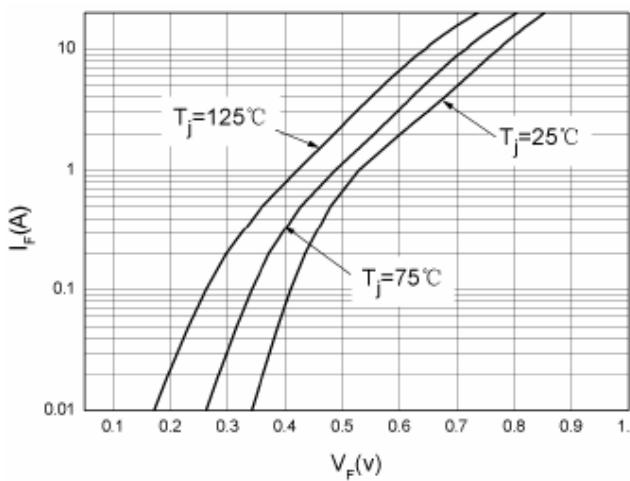


Fig.1 Forward voltage drop versus forward current (maximum values, per diode).

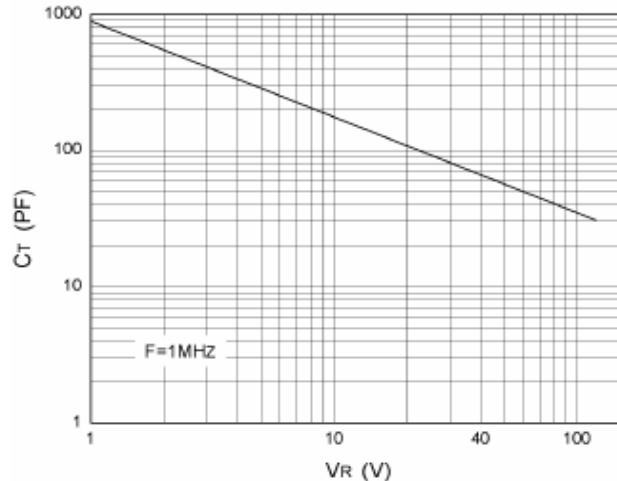


Fig.2 Junction capacitance versus reverse voltage applied (typical values, per diode).

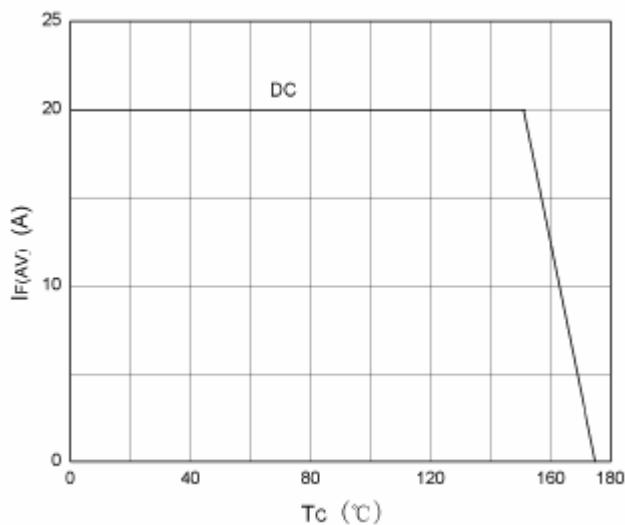


Fig.3 Average current versus ambient temperature ($d=0.5$) (per diode)

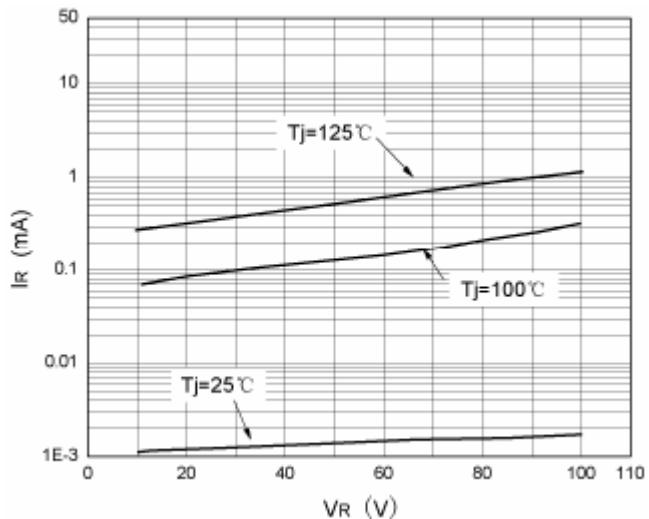
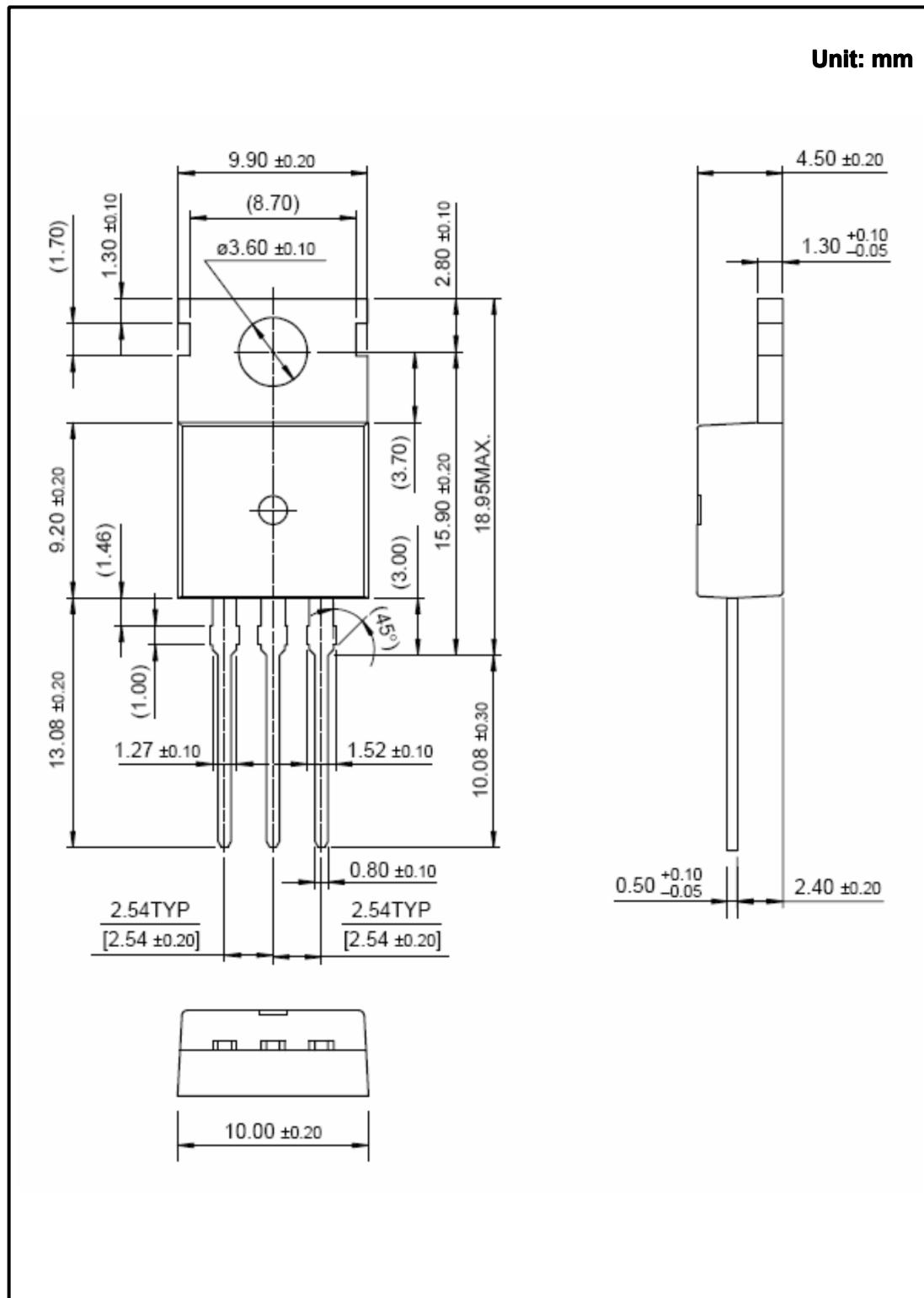


Fig.4 Reverse leakage current versus reverse voltage applied (typical values, per diode)..

TO-220 Package Dimension



TO-220HW Package Dimension